

Figure 1. The thickness of Al_2O_3 thin films on Si-H and Si-OH substrates at 200 °C deposited using trimethylaluminum (TMA), dimethylaluminum chloride (DMAC), or triethylaluminum (TEA) as a precursor and H_2O as a co-reactant. The thickness is measured using *in-situ* spectroscopic ellipsometry (SE).

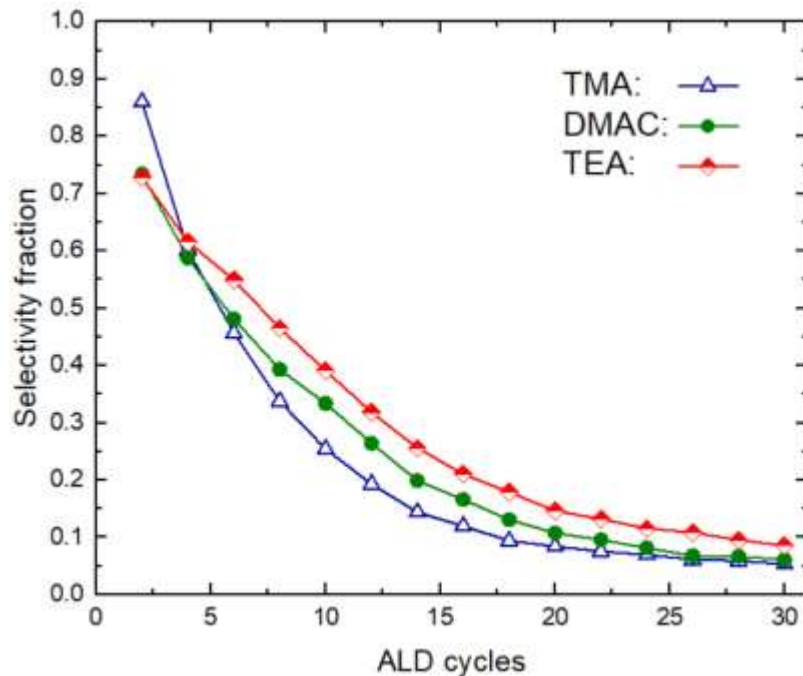


Figure 2. Calculated selectivity fraction values between Al_2O_3 films grown on Si-OH and Si-H starting surfaces using different Al precursor at 200 °C. The selectivity fraction is calculated as $(t_1 - t_2) / (t_1 + t_2)$, where t_1 is the film thickness on the Si-OH and t_2 the film thickness on the Si-H surface.